

**VERSION WITH MARKINGS TO SHOW CHANGES MADE**

**IN THE SPECIFICATION:**

A marked-up version of paragraph [0001], highlighting the changes thereto, follows:

[0001] Cross Reference to Related Applications: This application is a continuation of application Serial No. 09/392,153, filed September 8, 1999, [pending] now U.S.

Patent 6,265,775 B1, issued July 24, 2001, which is a divisional of application Serial No. 08/788,209, filed January 24, 1997, now U.S. Patent 6,221,753 B1, issued April 24, 2001.

IN THE CLAIMS:

A marked-up version of each of the presently amended claims, highlighting the changes thereto, follows:

1. (Twice Amended) An assembly comprising:  
a first semiconductor die having at least one lead on an active surface thereof, said at least one lead having at least one conductive pad disposed thereon, said at least one conductive pad having an upper surface, having a thickness and extending above said active surface of said first semiconductor die said thickness of said at least one conductive pad, said [first] semiconductor die substrate having a passivation layer disposed on said active surface thereof having a thickness greater than said thickness of said at least one conductive pad, said passivation layer having at least one via therein, said at least one conductive pad extending into and through only a portion of said at least one via, and said first semiconductor die having a layer of adhesive covering at least a portion of said passivation layer on said active surface, said layer of adhesive having a thickness; and  
a [second] substrate [die] having at least one lead on a facing surface thereof, said at least one lead of said [second] substrate [die] having at least one conductive pad disposed thereon, said at least one conductive pad of said [second] substrate [die] having an upper surface, having a thickness and extending above said facing surface of said [second] substrate [die], said thickness of said at least one conductive pad of said [second] substrate [die] being at least a combined thickness of said layer of adhesive covering at least a portion of said passivation layer on said active surface of said first semiconductor die and a remaining portion of said at least one via having said at least one conductive pad of said first semiconductor die extending thereinto; [wherein] said [second] substrate [die] being attached to said first semiconductor die by said adhesive layer of said first semiconductor die, said first semiconductor die having said upper surface of said at least one conductive pad on said at least one lead substantially forming movable, electrical contact without

mechanical attachment with said upper surface of said at least one conductive pad on said at least one lead of said [second] substrate [die], said movable electrical contact provided when said second substrate die is permanently attached to said first semiconductor die by said layer of adhesive.

2. (Twice Amended) The assembly of claim 1, wherein at least one of said active surface of said first semiconductor die and said facing surface of said [second] substrate [die] includes at least one groove thereon.

4. (Twice Amended) The assembly of claim 1, wherein at least one of said first semiconductor die and said [second] substrate [die] comprises a silicon wafer.

5. (Twice Amended) An assembly comprising:  
a first semiconductor die having at least one lead on an active surface thereof, said at least one lead having at least one conductive pad disposed thereon, said at least one conductive pad having an upper surface, having a thickness and extending above said active surface of said first semiconductor die said thickness of said at least one conductive pad, said first substrate having a passivation layer disposed on said active surface thereof having a thickness greater than said thickness of said at least one conductive pad, said passivation layer having at least one via therein, said at least one conductive pad extending into and through only a portion of said at least one via; and  
a [first] substrate having at least one lead on a facing surface thereof, said at least one lead of said [first] substrate having at least one conductive pad disposed thereon, said at least one conductive pad of said [first] substrate having an upper surface, having a thickness and extending above said facing surface of said second substrate, said thickness of said at least one conductive pad of said [first] substrate being at least a thickness of a remaining portion of said at least one via having said at least one conductive pad of said first

semiconductor die extending thereinto, said first semiconductor die being attached to said [second] substrate by an encapsulation material substantially surrounding said first semiconductor and a portion of said [second] substrate, said first substrate having said upper surface of said at least one conductive pad on said at least one lead of said first semiconductor die substantially forming movable, electrical contact without mechanical attachment with said upper surface of said at least one conductive pad on said at least one lead of said [first] substrate.

6. (Twice Amended) An assembly comprising:

- a [first] semiconductor wafer device having at least one lead on a first side thereof, said at least one lead having at least one conductive pad disposed thereon having a substantially flat surface thereon, having a thickness and extending above said first side of said [first] semiconductor [die] wafer device said thickness of said at least one conductive pad, said [first] semiconductor wafer device having a passivation layer disposed on said first side thereof having a thickness greater than said thickness of said at least one conductive pad, said passivation layer having at least one via therein, said at least one conductive pad extending into and through only a portion of said at least one via, and said [first] semiconductor wafer device having a layer of adhesive covering at least a portion of said passivation layer on said first side, said layer of adhesive having a thickness; and
- [a] at least one [first] semiconductor die having at least one lead on a first side thereof, said at least one lead of said [first substrate] semiconductor die having at least one conductive pad disposed thereon, said at least one conductive pad of said [first substrate] semiconductor die having a substantially flat surface thereon, having a thickness and extending above said first side of said [first substrate] semiconductor die, said thickness of said at least one conductive pad of said [first substrate] semiconductor die being at least a combined thickness of said layer of adhesive covering said at least a portion of said passivation layer on said first side of said [first] semiconductor wafer device and a

remaining portion of said at least one via having said at least one conductive pad of said [first] semiconductor wafer device extending thereinto, said [first] semiconductor wafer device [substrate] being juxtaposed to said first semiconductor die by said layer of adhesive, said [first] semiconductor wafer device having said substantially flat surface of said at least one conductive pad on said at least one lead of said [first] semiconductor wafer device forming movable, electrical contact without mechanical attachment with said substantially flat surface of said at least one conductive pad on said at least one lead of said [first substrate] semiconductor die, said movable, electrical contact provided when said [first substrate] semiconductor wafer device is permanently juxtaposed to said [first] semiconductor die [device] by said layer of adhesive.

7. (Twice Amended) A semiconductor assembly comprising:  
a first semiconductor substrate having at least one lead on a facing surface thereof, said at least one lead having at least one conductive pad disposed thereon, said at least one conductive pad having an upper surface, having a thickness and extending above said facing surface of said first substrate said thickness of said at least one conductive pad, said first substrate having a passivation layer disposed on said facing surface thereof having a thickness greater than said thickness of said at least one conductive pad, said passivation layer having at least one via therein, said at least one conductive pad extending into and through only a portion of said at least one via; and  
a second semiconductor substrate having at least one lead on a facing surface thereof, said at least one lead of said second substrate having at least one conductive pad disposed thereon, said at least one conductive pad of said second substrate having an upper surface, having a thickness and extending above said facing surface of said second substrate, said thickness of said at least one conductive pad of said second substrate being at least a thickness of a remaining portion of said at least one via having said at least one

conductive pad of said first substrate extending thereinto, one of said first substrate and said second substrate being attached to another one of said first substrate and said second substrate by a glob top covering said one of said first substrate and said second substrate and adhering to at least a portion of said facing surface of said another one of said first substrate and said second substrate, said one of said first substrate and said second substrate having said upper surface of said at least one conductive pad on said at least one lead thereof substantially forming movable, electrical contact without mechanical attachment with said upper surface of said at least one conductive pad on said at least one lead of said another one of said first substrate and said second substrate, said movable, electrical contact provided when said one of said first substrate and said second substrate is permanently attached to said another one of said first substrate and said second substrate by said glob top.

16. (Twice Amended) An assembly comprising:
- a silicon substrate having a plurality of leads on a first side thereof, each lead of said plurality of leads having a conductive pad disposed thereon in a substantially horizontal plane, each conductive pad having a substantially flat surface disposed in said substantially horizontal plane thereon, having a thickness and extending above said first side of said silicon substrate said thickness of said each conductive pad, said silicon substrate having a passivation layer disposed on said first side thereof having a thickness greater than said thickness of said each conductive pad, said passivation layer having at least one via therein for said each said conductive pad, said each conductive pad extending into and through only a portion of said at least one via, and said silicon substrate having a layer of adhesive covering at least a portion of said passivation layer on said first side, said layer of adhesive having a thickness; and
- [at least one semiconductor device] at least two semiconductor devices, each having a plurality of leads on a first side thereof, each lead of said plurality of leads [of said at least one

semiconductor device] having a conductive pad disposed thereon in a substantially horizontal plane, each conductive pad [of said at least one semiconductor device] having a substantially flat surface disposed in said substantially horizontal plane thereon, having a thickness and extending above said first side of a [said at least one] semiconductor device, said thickness of said each conductive pad of a [said at least one] semiconductor device being at least a combined thickness of said layer of adhesive covering at least a portion of said passivation layer on said first side of said silicon substrate and a remaining portion of said each at least one via having said each conductive pad of said silicon substrate extending thereinto, said at least two [one] semiconductor devices [device] being juxtaposed to said silicon substrate by said layer of adhesive, said silicon substrate having said conductive pad on at least one lead of said plurality of leads on said silicon substrate forming movable electrical contact without mechanical attachment with said conductive pad on at least one lead of said plurality of leads of a [said at least one] semiconductor device, said movable, electrical contact provided when a [said at least one] semiconductor device is permanently attached to said silicon substrate by said layer of adhesive.

17. (Twice Amended) The assembly of claim 16, wherein at least one of said first side of said silicon substrate and said first side of a [said at least one] semiconductor device includes at least one groove thereon.

19. (Twice Amended) The assembly of claim 16, wherein at least one of said silicon substrate and a [said at least one] semiconductor device comprises a silicon wafer.

20. (Twice Amended) An assembly comprising:
- a substrate having at least one lead on a facing surface thereof, said at least one lead having at least one conductive pad disposed thereon, said at least one conductive pad having an upper surface, having a thickness and extending above said facing surface of said substrate said thickness of said at least one conductive pad, said substrate having a passivation layer disposed on said facing surface thereof having a thickness greater than said thickness of said at least one conductive pad, said passivation layer having at least one via therein, said at least one conductive pad extending into and through only a portion of said at least one via; and
- at least one silicon semiconductor device having at least one lead on an active surface thereof having at least one bond pad disposed thereon, said at least one bond pad of said at least one silicon semiconductor device having an upper surface, having a thickness and extending above said active surface of said at least one silicon semiconductor device, said at least one silicon semiconductor device having a layer of adhesive having a thickness on at least a portion of said active surface thereof, said at least one silicon semiconductor device being attached to said substrate by said layer of adhesive, said upper surface of said at least one conductive pad on said at least one lead of said substrate substantially forming movable, electrical contact without mechanical attachment with said upper surface of said at least one bond pad on said at least one lead of said at least one silicon semiconductor device, said movable electrical contact provided when said at least one silicon semiconductor device is permanently attached to said substrate by said layer of adhesive.